



1.8V 20Gbps DP2.0 Linear ReDriver with AUX Listener & I2C Control

Features

- 4-to-4 Linear ReDriver[™] Channel Configuration with CTLE Gain Compensation up to 16dB @20Gbps
- Supports 4-lane DP2.0 (UHBR20/UHBR13/UHBR10)/HDBR3/ HBR2/RBR
- Ultra low Latency (< 300ps) for better Interoperability and Data throughput
- Individual Controls on CTLE Gain (6 to 16.2dB), Flat Gain (-4 to +2 dB)
- Integrated AUX Channel Listener for D3 Power Saving Mode
- I2C Slave Support with Speed up to 1MHz •
- Low Power DisplayPort Active (<350mW), D3 Power Down Mode (1.8mW)
- Single Power Supply: 1.8V +/-5%
- Industrial Temperature Support: -40°C to +85°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3) •
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Packaging (Pb-free & Green):

Tiny 32-pin, WLGA, 2.85 x 4.5 mm (0.4 mm pitch) (FLA)

Applications

- Laptop, Desktop and AIO PCs
- Workstation and Server
- **Docking Station**
- **Display Monitor**
- Gaming Console
- Active Cable

Description

The DIODES[™] PI2DPX2063 is a 20Gbps DP2.0/DP1.4 linear Re-Driver in a 4-to-4 configuration operated by a 1.8v power supply. The device supports UHBR20 (DP2.0 20Gbps), UHBR13.5 (DP2.0 13.5Gbps), UHBR10 (DP2.0 10Gbps), HBR3 (DP1.4 8.1Gbps), HBR2 (DP1.2 5.4Gbps), HBR(DP1.1 2.7Gbps) and RBR(DP1.0 1.62Gbps) under various DisplayPort speeds. With the on-chip AUX channel listener, the device can automatically monitor the system operation status to enter D3 power saving mode.

The non-blocking linear ReDriver design ensures that the differential signals conveying pre-shoot and de-emphasis equalization waveforms from the transmitter side to the receiver side help optimize the overall channel link adjustment conducted by the system transmitter and receiver that has been equipped with DFE. The CTLE equalizers are implemented at the inputs of the ReDriver to compensate the channel loss and reduce the ISI jitters. The programmable flat gain adjustments support the eye diagram opening.

The CTLE EQ gains and flat gains are individually programmable on each channel for flexible tuning via I2C register settings.

Ordering Information

Ordering Number	Package Code	Description
PI2DPX2063FLAEX	FLA	32-Pin, W-LGA4528-32
Notes:		

1. E = Pb-free and Green 2. X suffix = Tape/Reel

Notes:

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

ReDriver is a trademark of Diodes Incorporated.

^{1.} No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

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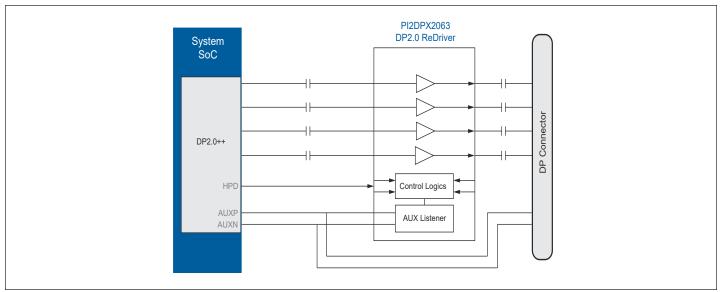


Revision History

Date	Revision	Description
August 2021	1	Preliminary Datasheet Release
		Updated Absolute Maximum Ratings Updated CTLE Equalization Gain
July 2022	2	Updated Feature Updated Configuration Table Updated Diodes Format



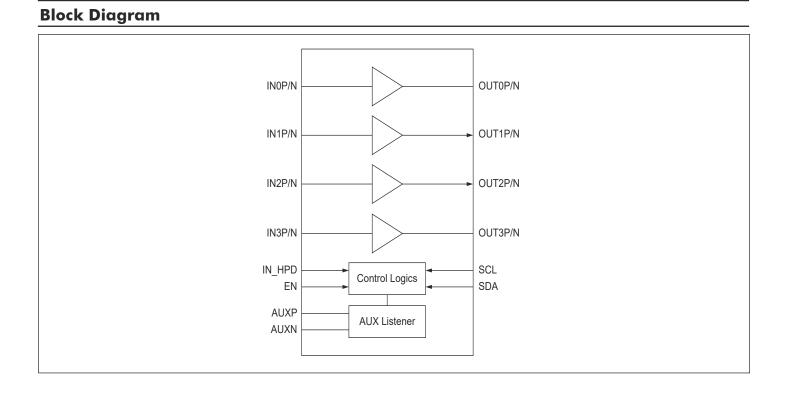




PI2DPX2063 in DP2.0 PC Motherboard Application



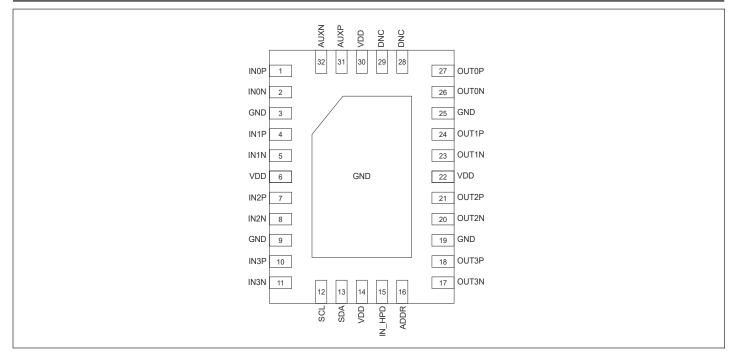








Pin Configuration (Top-Side View)



Pin Description

Pin #	Pin Name	Туре	Description					
Power and GND								
6, 14, 22, 30	VDD	Power	1.8V power supply, ±5%					
3, 9, 19, 25, Center Pad	GND	Ground	Supply ground					
Control Pins								
12	SCL	I	SCL is I2C control bus clock. Open drain structure.					
13	SDA	I/O	SDA is I2C control bus data. Open drain structure.					
	IN_HPD	Ι	Hot plug detection from Sink.					
15			With I2C (IN_HPD_HIZ) selectable internal 300k Ω pull-down resistor.					
			IN_HPD_HIZ='0', 300k Ω pull-down. Otherwise, the pin is HiZ					
16	ADDR	I	The I2C address select. 4-level input pin. With internal 100K Ω pull-up and 200K Ω pull-down resistors.					
			External Pulldown resistor value is $68 \mathrm{K}\Omega$.					
High Speed I/O Pin	ns							
18,	OUT3P,							
17	OUT3N		Channel CML output terminals.					
27,	OUT0P,	0	With selectable output termination between 50 Ω to VDD, 6k Ω to internal Vbi- asTx or Hi-Z					
26	OUT0N							





Pin Description Cont.

Pin #	Pin Name	Туре	Description	
21,	OUT2P,			
20	OUT2N		Channel CML output terminals.	
24,	OUT1P,	0	With selectable output termination between 50Ω to VDD, $6K\Omega$ to internal VbiasTx or Hi-Z	
23	OUT1N			
1,	INOP,			
2	INON	т	Channel CML input terminals.	
10,	IN3P,	I	With selectable input termination between 50Ω to internal VbiasRx, or $78K\Omega$ to internal VbiasRx.	
11	IN3N			
4,	IN1P,			
5	IN1N	т	Channel CML input terminals.	
7,	IN2P,	I	With selectable input termination between 50Ω to internal VbiasRx, or $78K\Omega$ to internal VbiasRx.	
8	IN2N			
Side Band Signal Pins				
29, 28	DNC		Do Not connect	
31, 32	AUXP, AUXN	I/O	DisplayPort AUX CH differential signal connections	





Operation Mode

Table 1. Configuration Table

OP_MODE<3:0>	IN0	IN1	IN2	IN3	AUXP	AUXN	Mode	
0000-0001	_	_	_	-	_	-	Reserved	
	OUT0	OUT1	OUT2	OUT3				
0010	(DP0)	(DP1)	(DP2)	(DP3)	_	-	4-lane DP + AUX	
0011	OUT0	OUT1	OUT2	OUT3	_	_	4-lane DP + AUX (flipped)	
0011	(DP3)	(DP2)	(DP1)	(DP0)		_	4-lane DI + AOA (inpped)	
<0100> ~ <1111>	_	_	_	-	_	—	Reserved	

Notes: 1) <0010> default at power on.

I/O Termination Resistance under Different Conditions

Symbol	Parameter	Resistance	Units
RX Terminal			
R _{in-pd}	Input res at EN=0	78k to GND	Ω
R _{in-Active}	Input res at active mode condition	50 to VbiasRx1	Ω
R _{in-DP-standby}	Input res in DP standby mode	78k to GND	Ω
R _{in-DP-active}	Input res in DP active mode	50 to VbiasRx1	Ω
R _{in-DP-D3}	Input res in DP D3 mode	78k to GND	Ω
TX Terminal			
R _{out-pd}	Output res at EN=0	78k to GND	Ω
Rout-Active	Output res at active mode condition	50 to VDD	Ω
Rout-DP-standby	Output res in DP standby mode	78k to GND	Ω
Rout-DP-active	Output res in DP active mode	50 to VDD	Ω
R _{out-DP-D3}	Output res in DP D3 mode	78k to GND	Ω

DisplayPort Mode

By default, all channels will go to active mode if HPD bit = 1. The ON/OFF of each DP channel is controlled by the Aux lane count.

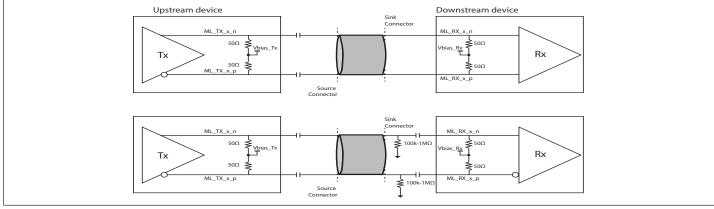


Figure 1. DisplayPort Main Link Connection Diagram





DisplayPort Main Link

The electrical sub-block of a DP Main-Link consists of up to four differential pairs. The DP TX drives doubly terminated, AC-coupled differential pairs in a manner compliant with the Main-Link Transmitter electrical specification.

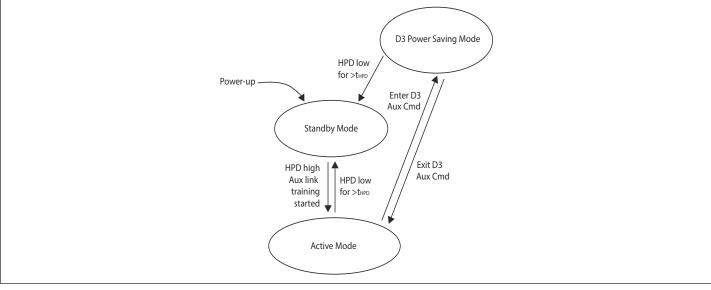


Figure 2. DisplayPort Operation Modes

,	Table 2. Des	cription of DP Operatin	g	Mode
. Г				

PM_State	Mode	Description
1 Standby Mode Low power consumption (AUX listener is OFF); Main Link outputs		Low power consumption (AUX listener is OFF); Main Link outputs are disabled
2	Active Mode	Data transfer (normal operation); AUX listener is active. The AUX listener is actively monitoring for Link Training unless it is disabled through I2C interface. After power-up and in active mode, all Main Link outputs are enabled. AUX Link Training is necessary to overwrite the DPCD registers to enable/disable Main Link outputs.
3	D3 Power Saving Mode	Low power consumption(AUX listener is active); Main Link outputs are disabled





CTLE Equalization, Flat Gain and Chip Enable Controls

Table 3. CTLE Equalization Gain (Typical Values at FG = 0dB)

I2C Register Setting EQ<2:0>			Equalizer Setting (dB)				
EQ<2>	EQ<1>	EQ<0>	@1.35GHz	@2.5GHz	@4GHz	@5GHz	@10GHz
0	0	0	-0.1 (Default)	0.1 (Default)	0.7 (Default)	1.3 (Default)	6.0 (Default)
0	0	1	0.0	0.6	1.6	2.5	8.5
0	1	0	0.2	1.3	2.8	4.1	10.8
0	1	1	0.6	2.2	4.3	5.8	12.7
1	0	0	1.1	3.5	6.0	7.7	14.2
1	0	1	1.7	4.8	7.6	9.3	15.2
1	1	0	2.6	6.3	9.2	10.8	15.8
1	1	1	3.5	7.5	10.4	11.8	16.2

Note: F: Floating, R: External resistor to ground.

Table 4. Flat Gain Setting (FG)

I2C Regist	er FG[1:0]	Flat Gain Setting
0	0	-4 dB
0 1		-2 dB
1	0	+0 dB (Default)
1	1	+2 dB





Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)

Storage Temperature65°C to +150°C
Junction Temperature
Supply Voltage to Ground Potential0.5V to VDD+0.3V
Voltage Input to High Speed Differential Pins0.5V to VDD
Voltage Input to Low Speed Pins (SCL, SDA)0.5V to +3.3V
Voltage Input to Low Speed Pins (AUXP/N)0.5V to +3.3V
ESD, HBM ±4000V
ESD, CDM±1000V

Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Thermal Information

Symbol	Parameter	32-Pin X2QFN Package	Units
Theta JA	Junction to Ambient Thermal Resistance	49.7	°C/W

Recommended Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Units
V _{DD}	Supply Voltage	1.71	1.8	1.89	V
V _{DD_Noise}	Power Supply Noise Up to 50MHz			50	mVpp
V _{RX_CM}	Input Source Common-Mode Noise			150	mVpp
Cac_coupling	System AC Coupling Capacitance	75		265	nF
T _A	Ambient Temperature	-40(1)		+85	°C

Note:

1. The minimum temperature -40°C guaranteed by design

Power Consumption

Symbol	Parameter	Min.	Тур.	Max.	Units
I _{ON_4DP}	4-lane DP2.0		160	220	mA
I _{D3}	Display Port D3 power down mode		1	1.6	mA
I _{ENB}	Disabled mode (EN= Low)		8	30	uA

AC/DC Characteristics $(VDD = 1.8 \pm 5\%, T_A = -40^{\circ}C \text{ to } 85^{\circ}C)$

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units				
V _{DD}	Supply Voltage	—	1.71	1.8	1.89	V				
Receiver (RX	Receiver (RX) (100 Ω differential) Electrical Specification									
R _{RX-DIFF-DC}	DC Differential Input Impedance		72		120	Ω				





Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
R _{RX-SINGLE-} DC	DC single ended input impedance to guarantee RxDet	Measured with respect to GND over a voltage of 500mV max	18		30	Ω
Z _{RX-HIZ-DC-} PD	DC input CM input impedance for V>0 during reset or power down	(Vcm=0 to 500mV)	25			kΩ
Cac_coupling	AC coupling capacitance		75		265	nF
V _{RX-CM-AC-P}	Rx common mode peak voltage	AC up to 5GHz			150	mVpeak
V _{RX-CM-DC-} Active-Idle- Delta-P	Common mode peak voltage AvgU0 (VTX-D+ + VTX-D-)/2 –AvgU1 (VTX-D+ + VTX-D-)/2				200	mVpeak
Transmitter	(TX) Electrical Specification					
V _{TX-DIFF-PP}	Output differential p-p voltage Swing	Differential Swing V _{TX-D+} - V _{TX-D-}		1		Vppd
R _{TX-DIFF-DC}	DC Differential TX Impedance		72		120	Ω
V _{TX-RCV-DET}	The amount of Voltage change al- lowed during RxDet	Type-C Tx Spec +/-60mA			600	mV
Cac-coupling	AC coupling capacitance		75		265	nF
R _{TX-DC-CM}	Common mode DC output Imped- ance		18		30	Ω
I _{TX-SHORT}	Transmitter short circuit current limit				60	mA
V _{TX-C}	Common-Mode Voltage	$ V_{TX-D+} + V_{TX-D-} /2$	VDD-1V		VDD	V
V _{TX-DC-CM}	Instantaneous allowed DC com- mon mode voltage at the connector side of the AC coupling capacitors	$ V_{TX-D+} + V_{TX-D-} /2$	0		VDD	V
V _{TX-CM-AC-} PP-Active	Active mode TX AC common mode voltage	$V_{TX-D+} + V_{TX-D-}$ for both time and amplitude			100	mVpp
VTX-Idle-Diff- AC-pp	Idle mode AC common mode delta voltage V _{TX-D+} –V _{TX-D-}	Between D+ and D- in idle mode. Use the HPF to remove DC components. =1/LPF.			10	mVppd
V _{TX-Idle-Diff-} DC	Idle mode DC common mode delta voltage V _{TX-D+} –V _{TX-D-}	Between D+ and D- in idle mode. Use the LPF to remove AC components. =1/HPF.			10	mV
Channel Perf	formance					
T _{pd}	Latency	From input to output		25	150	ps





AC/DC Characteristics Cont.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units	
		EQ<2:0> = 000		6			
		EQ<2:0> = 001		8.5			
		EQ<2:0> = 010		10.8			
	Peaking gain (Compensation	EQ<2:0> = 011		12.7		dF	
G _{P_USB}	at 10GHz, relative to 100MHz,	EQ<2:0> = 100		14.2		dB	
	100mV _{p-p} sine wave input)	EQ<2:0> = 101		15.2			
		EQ<2:0> = 110		15.8			
		EQ<2:0> = 111		16.2			
		Variation around typical	-2		+2	dB	
		FG<1:0> = 00		-4			
		FG<1:0> = 01		-2		10	
G _F	Flat gain (100MHz, EQ<2:0>=000)	FG<1:0> = 10		0		dB	
GP_USB GF Vsw_100M Vsw_10G DDNEXT DDFEXT ⁽²⁾ VNOISE_IN VNOISE_IN VNOISE_OUT S11DM S11CM		FG<1:0> = 11		+2			
		Variation around typical	-2		+2 dB +2 dB 910 mVppo	dB	
V _{sw_100M}	Output linear swing (at 100MHz)	EQ<2:0>=000		910		mVppd	
V _{sw_10G}	Output linear swing (at 10GHz)	EQ<2:0>=000		800		mVppd	
DDNEXT	Differential near-end crosstalk	100MHz to 10GHz, Fig. 6		-30		dB	
DDFEXT ⁽²⁾	Differential far-end crosstalk	100MHz to 10GHz, Fig. 7		-30		dB	
		100MHz to 10GHz, EQ<2:0>=000, FG<1:0>=10, Fig. 8		0.6			
V NOISE_IN	Input-referred noise	100MHz to 10GHz, EQ<2:0>=111, FG<1:0>=10, Fig. 8		0.3		mV _{RMS}	
X7	Output of and a size	100MHz to 10GHz, EQ<2:0>=000, FG<1:0>=10, Fig. 8		0.3			
V NOISE_OUT	Output-referred noise	100MHz to 10GHz, EQ<2:0>=111, FG<1:0>=10, Fig. 8		0.5		- mV _{RMS}	
S11DM	Input differential mode return loss	10MHz to 10GHz differential mode	-11.5 -8.1		dB		
S11CM	Input common mode return loss	1GHz to 10GHz common mode	-10 -5		dB		
S22DM	Output differential mode return loss	10MHz to 10GHz differential mode		-12.5	-8.1	dB	
S22CM	Output common mode return loss	1GHz to 10GHz common mode		-8	-4	dB	





AC/DC Characteristics Cont.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
DisplayPort	Electrical Specification					
V _{TX-C}	Common-Mode Voltage	$ V_{TX-D+} + V_{TX-D-} /2$	VDD-1V		VDD	V
V _{TX-AC-CM} HBR_RBR	TX AC common mode voltage for HRB and RBR	Measured using an 8b/10b			20	mVrms
V _{TX-AC-} CM_HBR2	TX AC common mode voltage for HBR2	pattern with 50% transition density			30	mVrms
V _{TX-DIFFp-p-} Level0	Differential peak-to-peak output voltage swing Level 0	Tested with Pre-emphasis at Level 0= 0dB Level 1= 3.5dB Level 2= 6.0 dB	0.34	0.4	0.46	V
V _{TX-DIFFp-p-} Level1	Differential peak-to-peak output voltage swing Level 1		0.51	0.6	0.68	V
V _{TX-DIFFp-p-} Level2	Differential peak-to-peak output voltage swing Level 2		0.69	0.8	0.92	V
	UHBR20(20Gbps) TP2				0.45	UI
F	UHBR13(13.5Gbps) TP2				0.45	UI
	UHBR10(10Gbps) TP2	Measured at Transmit output.			0.38	UI
Tj TX Total Iitter	HBR3 (8.1Gbps)	Prechannel loss from 2.5dB			0.27	UI
Jitter	HBR2 (5.4Gbps)	to 13dB			0.27	UI
	HBR (2.7Gbps)	-			0.294	UI
	RBR (1.62Gbps)				0.18	UI
AUX Listene	er Electrical Specification					
C _{in}	Input capacitance at AUXP or AUXN				10	pF
VT _{(AUX_lis-} tener)	Threshold of the AUX listener	VCC = 1.8V	100		220	mVPPd

Note:

1. Measured using a vector-network analyzer (VNA) with -30dBm power level applied to the adjacent input. The VNA detects the signal at the output of the victim channel. All other inputs and outputs are terminated with 50Ω .

2. Subtract the channel gain from the total gain to derive the actual crosstalk





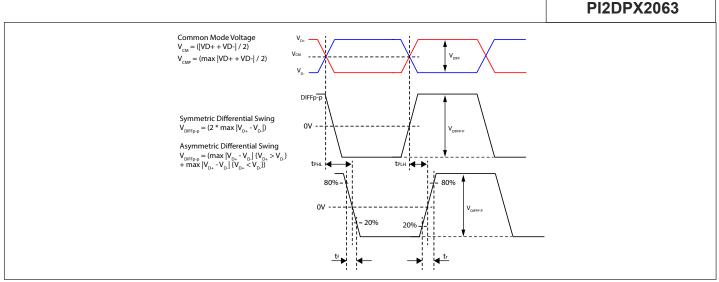


Figure 4. Definition of Peak-to-peak Differential Voltage

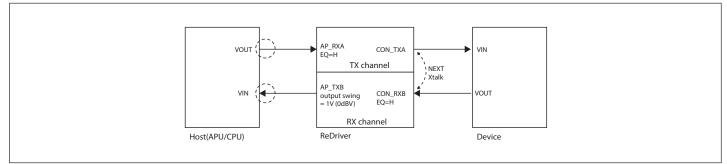


Figure 5. NEXT Crosstalk Definition

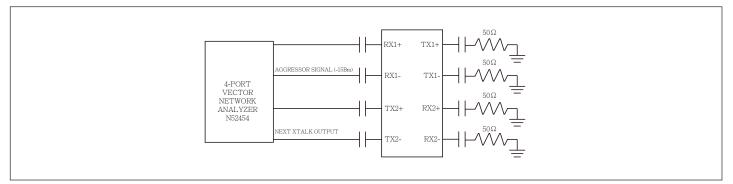


Figure 6. NEXT Channel-isolation Test Configuration





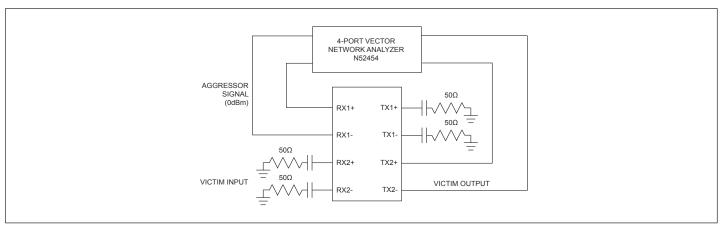


Figure 7. NEXT Channel-isolation Test Configuration

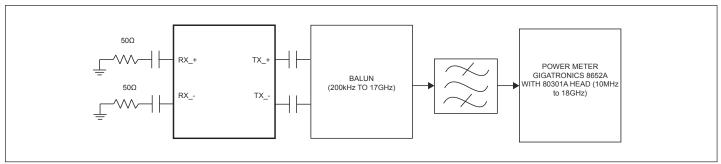


Figure 8. Noise Test Configuration

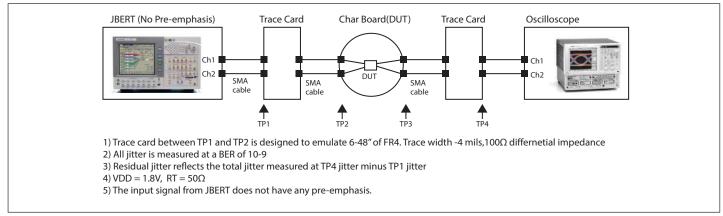


Figure 9. Channel Measurement Setup





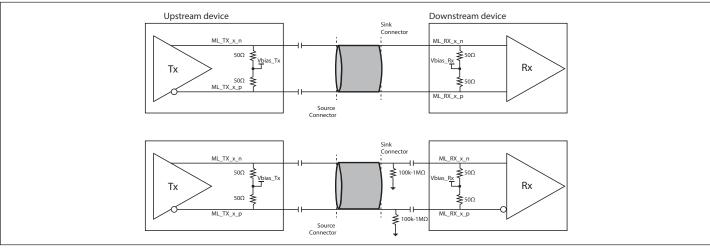


Figure 10. High-speed Channel Test Circuit

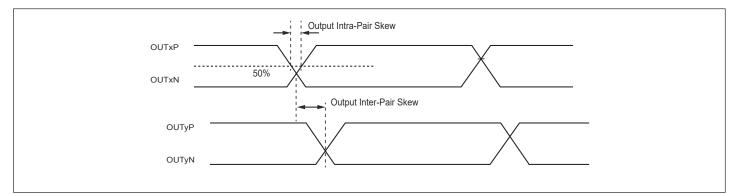


Figure 11. Intra and Inter-pair Differential Skew Definition





I2C Electrical Specification and Timing

Characteristics of the SDA	and SCL I/O Stages
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			This S	ilicon	Fast-Mo	IIn:to	
Symbol	Parameter	Conditions	Min.	Max.	Min.	Max.	Units
V _{IL}	LOW-level input voltage		-0.5	$0.3 V_{DD}$	-0.5	$0.3 V_{DD}$	V
V _{IH}	HIGH-level input voltage		$0.7 V_{DD}$		$0.7 V_{DD}$		V
V _{hys}	Hysteresis of Schmitt trigger inputs		0.05V _{DD}		0.05V _{DD}		V
V _{OL1}	LOW-level output voltage 1	Open-drain or open-col- lector at 3mA sink current; V _{DD} >2V	0	0.4	0	0.4	V
I _{OL}	LOW-level output current	V _{OL} =0.4V	20		20		mA
t _{of}	output fall time from V_{IHmin} to V_{ILmax}		12	120	20×(V _{DD} /5.5V)	120	ns
t _{SP}	Pulse width of spikes that must be suppressed by the input filter		0	50	0	50	ns
Ii	Input current each I/O pin	$0.1 V_{DD} < V_I < 0.9 V_{DDmax}$	-10	+10	-10	+10	uA
Ci	Capacitance for each I/O pin			10		10	pF

Characteristics of the SDA and SCL Bus Lines the Devices

			This S	Silicon	Fast-Mo	TT	
Symbol	Parameter	Conditions	Min.	Max.	Min.	Max.	- Units
f _{SCL}	SCL clock frequency		10	1000	0	1000	kHz
t _{HD;STA}	Hold time (repeated) START condition	After this period, the first clock pulse is generated.	0.26		0.26		us
t _{LOW}	LOW period of the SCL clock		0.5		0.5		us
t _{HIGH}	HIGH period of the SCL clock		0.26		0.26		us
t _{SU;STA}	Set-up time for a repeated START condition		0.26		0.26		us
t _{SU;DAT}	Data set-up time		50		50		ns
t _r	Rise time of both SDA and SCL signals			120		120	ns
tf	Fall time of both SDA and SCL signals		12	120	20×(V _{DD} /5.5V)	120	ns
t _{SU;STO}	Set-up time for STOP condi- tion		0.26		0.26		us
t _{BUF}	Bus free time between a STOP and START condition		0.5		0.5		us





Characteristics of the SDA and SCL Bus Lines the Devices Cont.

Symbol	Parameter	Conditions -	This Silicon		Fast-Mo	IIn:to	
Symbol			Min.	Max.	Min.	Max.	Units
C _b	Capacitive load for each bus line			550		550	pF
t _{VD;DAT}	Data valid time			0.45		0.45	us
t _{VD;ACK}	Data valid acknowledge time			0.45		0.45	us
V _{nL}	Noise margin at the LOW level	For each connected device (including hysteresis)	$0.1 \mathrm{V_{DD}}$		$0.1 V_{DD}$		V
V _{nH}	Noise margin at the HIGH level	For each connected device (including hysteresis)	$0.2 \mathrm{V_{DD}}$		$0.2 \mathrm{V_{DD}}$		V

Reference Electrical Specification and Timing (Extracted from I2C specification Rev2.6) Characteristics of the SDA and SCL I/O Stages

0 1 1	Parameter		Standar	d-Mode	Fast-Mode		Fast-Mode Plus		TT
Symbol	Parameter	Conditions	Min.	Max.	Min.	Max.	Min.	Max.	Units
V _{IL}	LOW-level input voltage ⁽¹⁾		-0.5	$0.3 V_{\rm DD}$	-0.5	$0.3 V_{DD}$	-0.5	$0.3 V_{\rm DD}$	V
V _{IH}	HIGH-level input voltage ⁽¹⁾		$0.7 V_{\text{DD}}$	(2)	$0.7 V_{DD}$	(2)	$0.7 \mathrm{V_{DD}}^{(1)}$	(2)	V
V _{hys}	Hysteresis of Schmitt trigger inputs				$0.05 V_{DD}$		$0.05 V_{DD}$		V
V _{OL1}	LOW-level output voltage 1	Open-drain or open- collector at 3mA sink current; V _{DD} > 2V	0	0.4	0	0.4	0	0.4	V
V _{OL2}	LOW-level output voltage 2	Open-drain or open- collector at 2mA sink current ⁽³⁾ ; $V_{DD} \le 2V$			0	$0.2V_{DD}$	0	$0.2 V_{DD}$	V
T		$V_{OL} = 0.4 V$	3		3		20		
I _{OL}	LOW-level output current	$V_{OL} = 0.6 V^{(4)}$			6				mA
t _{of}	Output fall time from V _{IHmin} to V _{ILmax}			250(5)	20×(V _{DD} /5.5V) ⁽⁶⁾	250(5)	20×(V _{DD} /5.5V) ⁽⁶⁾	120(7)	ns
t _{SP}	Pulse width of spikes that must be suppressed by the input filter				0	50 ⁽⁸⁾	0	50 ⁽⁸⁾	ns
Ii	Input current each I/O pin	0.1V _{DD} <v<sub>I < 0.9V_D_ Dmax</v<sub>	-10	+10	-10 ⁽⁹⁾	+10 ⁽⁹⁾	-10 ⁽⁹⁾	+10 ⁽⁹⁾	μΑ
Ci	Capacitance for each I/O pin ⁽¹⁰⁾			10		10		10	pF

Note:

1. Some legacy Standard-mode devices had fixed input levels of V_{IL} = 1.5V and V_{IH} = 3.0V. Refer to component datasheet.

2. Maximum $V_{IH} = V_{DD(max)} + 0.5V$ or 5.5V, which ever is lower. See component datasheet.

3. The same resistor value to drive 3mA at 3.0V V_{DD} provides the same RC time constant when using $< 2V V_{DD}$ with a smaller current draw.

4. In order to drive full bus load at 400kHz, 6mA IOL is required at 0.6V VOL. Parts not meeting this specification can still function, but not at 400kHz and 400pF. 5. The maximum t_f for the SDA and SCL bus lines quoted in Table 10 (300ns) is longer than the specified maximum t_{of} for the output stages (250ns). This allows series protection resistors (R_S) to be connected between the SDA/SCL pins and the SDA/SCL bus lines as shown in Figure 45 without exceeding the maximum specified t_f. 6. Necessary to be backwards compatible with Fast-mode.





7. In Fast-mode Plus, fall time is specified the same for both output stage and bus timing. If series resistors are used, designers should allow for this when considering bus timing.

8. Input filters on the SDA and SCL inputs suppress noise spikes of less than 50ns.

9. If $V_{\rm DD}$ is switched off, I/O pins of Fast-mode and Fast-mode Plus device must not obstruct the SDA and SCL lines.

10. Special purpose device such as multiplexers and switches may exceed this capacitance because they connect multiple paths together.

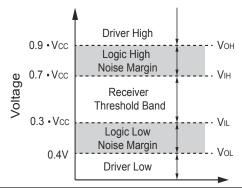


Figure 12. I2C I/O Stage Noise Margin

Characteristics of the SDA and SCL Bus Line for Standard, Fast, and Fast-mode Plus I2C-bus Device (1)

- I I			Standar	rd-Mode	Fast-M	lode	Fast-Mode Plus		T T 1 /
Symbol	Parameter	Conditions	Min.	Max.	Min.	Max.	Min.	Max.	Units
f _{SCL}	SCL clock frequency		0	100	0	400	0	1000	KHz
t _{HD;STA}	Hold time (repeated) START condition	After this period, the first clock pulse is generated.	4.0		0.6		0.26		μs
t _{LOW}	LOW period of the SCL clock		4.7		1.3		0.5		μs
t _{HIGH}	HIGH period of the SCL clock		4.0		0.6		0.26		μs
t _{SU;STA}	Set-up time for a repeated START condition		4.7		0.6		0.26		μs
t _{HD;DAT}	Data hold time ⁽²⁾	CBUS compatible masters	5.0						μs
		I2C-Bus Devices	0(3)	(4)	0(3)	(4)	0		
t _{SU;DAT}	Data set-up time		250		100(5)		50		ns
t _r	Rise time of both SDA and SCL signals			1000	20	300		120	ns
t _f	Fall time of both SDA and SCL signals ⁽³⁾⁽⁶⁾⁽⁷⁾⁽⁸⁾			300	20×(V _{DD} /5.5V)	300	20×(V _{DD} /5.5V) ⁽⁹⁾	120(8)	ns
t _{SU;STO}	Set-up time for STOP condi- tion		4.0		0.6		0.26		μs
t _{BUF}	Bus free time between a STOP and START condition		4.7		1.3		0.5		μs
C _b	Capacitive load for each bus line ⁽¹⁰⁾			400		400		550	pF
t _{VD;DAT}	Data valid time ⁽¹¹⁾			3.45 ⁽⁴⁾		0.9(4)		0.45 ⁽⁴⁾	μs





6	Description		Standard-Mode		Fast-Mode		Fast-Mode Plus		TT •/
Symbol	Parameter	Conditions	Min.	Max.	Min.	Max.	Min.	Max.	Units
t _{VD;ACK}	Data valid acknowledge time ⁽¹²⁾			3.45 ⁽⁴⁾		0.9(4)		0.45 ⁽⁴⁾	μs
V _{nL}	Noise margin at the LOW level	For each connected device (including hysteresis)	0.1V _{DD}		0.1V _{DD}		0.1V _{DD}		V
V _{nH}	level	For each connected device (including hysteresis)	0.2V _{DD}		0.2V _{DD}		0.2V _{DD}		V

Note:

1. All values referred to $\rm V_{IH(min)}$ (0.3V_{DD}) and $\rm V_{IL(max)}$ (0.7V_{DD}) levels.

2. t_{HD:DAT} is the data hold time that is measured from the falling edge of SCL, applies to data in transmission and the acknowledge.

3. A device must internally provide a hold time of at least 300ns for the SDA signal (with respect to the VIH(min) of the SCL signal) to bridge the undefined region of the falling edge of SCL.

4. The maximum t_{HD:DAT} could be 3.45µs and 0.9µs for Standard-mode and Fast-mode, but must be less than the maximum of t_{VD:DAT} or t_{VD:ACK} by a transition time. This maximum must only be met if the device does not stretch the LOW period (tLOW) of the SCL signal. If the clock stretches the SCL, the data must be valid by the set-up time before it releases the clock.

5. A Fast-mode I²C-bus device can be used in a Standard-mode I²C-bus system, but the requirement t_{SU:DAT} 250ns must then be met. This will automatically be the case if the device does not stretch the LOW period of the SCL signal. If such a device does stretch the LOW period of the SCL signal, it must output the next data bit to the SDA line $t_{r(max)} + t_{SU:DAT} = 1000 + 250 = 1250$ (according to the Standard-mode I²C-bus specification) before the SCL line is released. Also the acknowledge timing must meet this set-up time.

6. If mixed with Hs-mode device, faster fall times according to Table XX are allowed.

7. The maximum tf for the SDA and SCL bus lines is specified at 300ns. The maximum fall time for the SDA output stage tf is specified are 250ns. This allows series protection resistors to be connected in between the SDA and the SCL pins and the SDA/SCL bus lines without exceeding the maximum specified tf.

8. In Fast-mode Plus, fall time is specified the same for both output stage and bus timing. If series resistors are used, designers should allow for this when considering bus timing.

9. Necessary to be backwards compatible to Fast-mode.

10. The maximum bus capacitance allowable may vary from this value depending on the actual operating voltage and frequency of the application. Section XX discusses techniques for coping with higher bus capacitances.

11. t_{VS:DAT} = time for data signal from SCL LOW to SDA output (HIGH or LOW, depending on which one is worse).

12. t_{VS:ACK} = time for Acknowledgement signal from SCL LOW to SDA output (HIGH or LOW, depending on which one is worse).

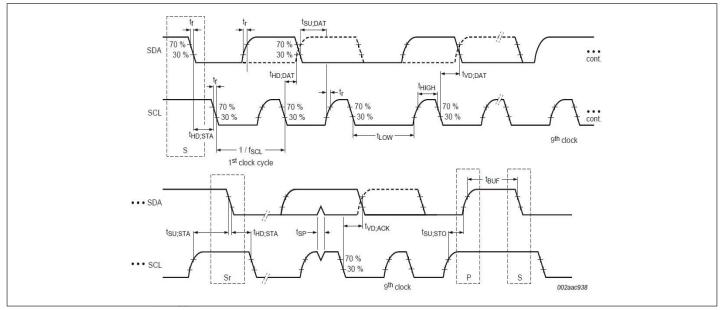


Figure 13. Definition of Timing for F/S-mode Devices on the I2C Bus





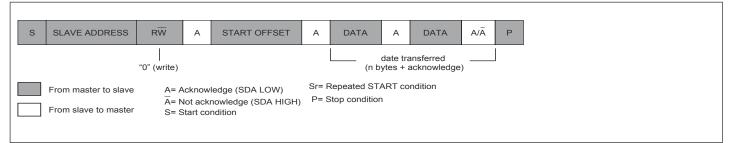
Detailed Programming Registers

I2C Slave Address Selections

	I2C Slave Address Assignment						
A6	A5	A4	A3	A2	A1	A0	ADDR (Pin 16)
1	0	1	0	0	0	0	L
1	0	1	0	0	0	1	М
1	0	1	0	0	1	0	F
1	0	1	0	0	1	1	Н



Indexed Read



Indexed Write

I2C Register Definitions

BYTE 0 (Rev	BYTE 0 (Revision and Vendor ID Register)					
Bit	Туре	Power-up Condition	Comment			
7	RO	0				
6	RO	0				
5	RO	0	Revision ID = 0000			
4	RO	0				
3	RO	0				
2	RO	0				
1	RO	1	Diodes ID = 0011			
0	RO	1				





BitTypePower-up ConditionComment7RO06RO05RO04RO13RO02RO11RO00RO0	BYTE 1 (De	BYTE 1 (Device Type/Device ID Register)					
6RO05RO04RO13RO02RO11RO0	Bit	Туре	Power-up Condition	Comment			
5RO04RO13RO02RO11RO0	7	RO	0				
5 RO 0 4 RO 1 3 RO 0 2 RO 1 1 RO 0	6	RO	0				
3 RO 0 2 RO 1 1 RO 0	5	RO	0	Device Type = Active Mux			
2 RO 1 1 RO 0	4	RO	1				
1 RO 0 Device ID	3	RO	0				
1 RO 0	2	RO	1				
0 RO 0	1	RO	0				
	0	RO	0				

BYTE 2 (Byte Count Register 32 Bytes)

Bit	Туре	Power-up Condition	Comment
7	RO	0	
6	RO	0	
5	RO	1	
4	RO	0	10C Desister Date Count 22 hotes
3	RO	0	I2C Register Byte Count = 32 bytes
2	RO	0	
1	RO	0	
0	RO	0	

BYTE 3 (Channel Assignment of RXDET_EN#)

Bit	Туре	Power-up Condition	Comment
7	R/W	0	
6	R/W	0	Operation Mode Setting
5	R/W	1	Refer to Table Configuration Table
4	R/W	0	
3	R/W	0	Reserved
2	R/W	0	Reserved
1	R/W	0	Reserved
0	R/W	0	Reserved





BYTE 4 (Ov	BYTE 4 (Override the Power Down Control)					
Bit	Туре	Power-up Condition	Comment			
7	R/W	0	CON3 power down override 0 – Do not force the CON3 to power down state 1 – Force the CON3 to power down state			
6	R/W	0	CON2 power down override 0 – Do not force the CON2 to power down state 1 – Force the CON2 to power down state			
5	R/W	0	CON1 power down override 0 – Do not force the CON1 to power down state 1 – Force the CON1 to power down state			
4	R/W	0	CON0 power down override 0 – Do not force the CON0 to power down state 1 – Force the CON0 to power down state			
3	R/W	0				
2	R/W	1	Reserved			
1	R/W	0				
0	R/W	0				
BYTE 5 (Eq	BYTE 5 (Equalization and Flat Gain Setting of CON0)					
Bit	Туре	Power-up Condition	Comment			
7	R/W	0	Reserved			
6	R/W	0	CON0_EQ<2> Equalizer setting			
5	R/W	0	CON0_EQ<1> Equalizer setting			
4	R/W	0	CON0_EQ<0> Equalizer setting			

CON0_FG<1> Flat gain setting

CON0_FG<0> Flat gain setting

Reserved

Reserved

3

2

1

0

R/W

R/W

R/W

R/W

1

0

0

0





BYTE 6 (Eq	YTE 6 (Equalization and Flat Gain Setting of CON1)				
Bit	Туре	Power-up Condition	Comment		
7	R/W	0	Reserved		
6	R/W	0	CON1_EQ<2> Equalizer setting		
5	R/W	0	CON1_EQ<1> Equalizer setting		
4	R/W	0	CON1_EQ<0> Equalizer setting		
3	R/W	1	CON1_FG<1> Flat gain setting		
2	R/W	0	CON1_FG<0> Flat gain setting		
1	R/W	0	Reserved		
0	R/W	0	Reserved		
BYTE 7 (Eq	BYTE 7 (Equalization and Flat Gain Setting of CON2)				
Bit	Туре	Power-up Condition	Comment		
7	R/W	0	Reserved		
6	R/W	0	CON2_EQ<2> Equalizer setting		
5	R/W	0	CON2_EQ<1> Equalizer setting		
4	R/W	0	CON2_EQ<0> Equalizer setting		
3	R/W	1	CON2_FG<1> Flat gain setting		
2	R/W	0	CON2_FG<0> Flat gain setting		
1	R/W	0	Reserved		
0	R/W	0	Reserved		
BYTE 8 (Eq	ualization and	l Flat Gain Setting of CO	N3)		
Bit	Туре	Power-up Condition	Comment		
7	R/W	0	Reserved		
6	R/W	0	CON3_EQ<2> Equalizer setting		
5	R/W	0	CON3_EQ<1> Equalizer setting		
4	R/W	0	CON3_EQ<0> Equalizer setting		
3	R/W	1	CON3_FG<1> Flat gain setting		
2	R/W	0	CON3_FG<0> Flat gain setting		
1	R/W	0	Reserved		
0	R/W	0	Reserved		





BYTE 9 (AU	3YTE 9 (AUX Flip Control)					
Bit	Туре	Power-up Condition	Comment			
7	R/W	0	Reserved			
6	R/W	0	Reserved			
5	R/W	0	Reserved			
4	R/W	0	Reserved			
3	R/W	0	Reserved			
2	R/W	0	Reserved			
1	R/W	0	AUX flip for AUXSBU1/2 and AUXP/N 0 – Flip is disabled 1 – Flip is enabled			
0	R/W	0	DP FLIP DP flip for ALL CONx channels 0 – DP Flip is Disabled 1 – DP Flip is Enabled			

BYTE 10 (Reserved)

Bit	Туре	Power-up Condition	Comment
7	R/W	1	
6	R/W	1	
5	R/W	1	
4	R/W	1	- D
3	R/W	1	Reserved
2	R/W	1	
1	R/W	0	
0	R/W	0	

BYTE 11 (Reserved)

Bit	Туре	Power-up Condition	Comment
7	R/W	1	
6	R/W	1	
5	R/W	1	
4	R/W	1	Reserved
3	R/W	1	Keserved
2	R/W	1	
1	R/W	0	
0	R/W	0	





BYTE 12 (R	BYTE 12 (Reserved)					
Bit	Туре	Power-up Condition	Comment			
7	R/W	0				
6	R/W	0				
5	R/W	1				
4	R/W	1				
3	R/W	0	Reserved			
2	R/W	0				
1	R/W	0				
0	R/W	1				
DVTE 12 (D						

BYTE 13 (Power State of the Channel CON0/1)

Bit	Туре	Power-up Condition	Control Affected	Comment
7	RO	N/A	CON0_State<2>	For the channel operating mode
6	RO	N/A	CON0_State<1>	000 – PD (Power down mode)
5	RO	N/A	CON0_State<0>	001 – PowerON (Power on ramping mode)
4	RO	N/A	Reserved	010 – UPM_Short (UPM less than 328ms)
3	RO	N/A	CON1_State<2>	011 – UPM_Long (UPM more than 328ms)
2	RO	N/A	CON1_State<1>	100 - UPM_Active (Unplug active mode)
1	RO	N/A	CON1_State<0>	101 - DSM (U1/U2/U3 power saving mode)
0	RO	N/A	Reserved	– 110 – SM (Slumber Mode) 111 - AM (active mode)

BYTE 14 (Power State of the Channel CON2/3)

Bit	Туре	Power-up Condition	Control Affected	Comment
7	RO	N/A	CON2_State<2>	For the channel operating mode
6	RO	N/A	CON2_State<1>	000 – PD (Power down mode)
5	RO	N/A	CON2_State<0>	001 – PowerON (Power on ramping mode)
4	RO	N/A	Reserved	010 – UPM_Short (UPM less than 328ms)
3	RO	N/A	CON3_State<2>	011 – UPM_Long (UPM more than 328ms)
2	RO	N/A	CON3_State<1>	100 - UPM_Active (Unplug active mode)
1	RO	N/A	CON3_State<0>	101 - DSM (U1/U2/U3 power saving mode)
0	RO	N/A	Reserved	110 – SM (Slumber Mode) 111 - AM (active mode)





BYTE 15 (L	FPS Detector	Monitor and Channel Po	wer Down Monitor)					
Bit	Туре	Power-up Condition	Comment					
7	RO	N/A	CON3_USB_LFPS#	Has meaning for USB3.x application				
6	RO	N/A	CON2_USB_LFPS#only. CONx_USB_LFPS#CON1_USB_LFPS#0-LFPS data					
5	RO	N/A						
4	RO	N/A	CON0_USB_LFPS#	1-5/10Gbps USB3.x data				
3	RO	N/A	PD_CON3_MON					
2	RO	N/A	PD_CON2_MON	Monitors the PD condition of each				
1	RO	N/A	PD_CON1_MON	channel.				
0	RO	N/A	PD_CON0_MON					
BYTE 16 (A	UX and HPD	Monitor)						
Bit	Туре	Power-up Condition	Comment					
7	RO	N/A	Reserved					
6	RO	N/A	Reserved					
5	RO	N/A	AUX_IDLE_DET# Detect the AUX activities "0" – Idle "1" – has activities					
4	RO	N/A	DP_HPD The condition of IN_HPD 0 – De-asserted 1 – Asserted Notes: When DP_HPD_PIN_EN	#=1, then, this value is 1 always.				
3	RO	N/A	AP0_RX_SEL "0" AP0 is TX terminal. "1" AP0 i	s RX terminal				
2	RO	N/A	AP3_RX_SEL "0" AP3 is TX terminal. "1" AP3 i	s RX terminal				
1	RO	N/A	CON0_RX_SEL "0" CON0 is TX terminal. "1" CO	N0 is RX terminal				
0	RO	N/A	CON3_RX_SEL "0" CON3 is TX terminal. "1" CON3 is RX terminal					





BYTE 17			
Bit	Туре	Power-up Condition	Comment
7	RO	0	
6	RO	0	
5	RO	0	
4	RO	1	
3	RO	0	Reserved
2	RO	1	
1	RO	0	
0	RO	0	
BYTE 18 (D	PCD Address	00101h: Lane Count Set)	
Bit	Туре	Power-up Condition	Comment
7	RO	0	LANE_COUNT_SET
6	RO	0	Main-Link Lane Count = Value.
5	RO	0	Bit<4:0>LANE_COUNT_SET
4	RO	0	Three values are supported. All other values are RESERVED.
3	RO	0	Note: Because the upstream device is required to set this value within the MAX_LINK_RATE register (DPCD Address 00001h), there is no power-on
2	RO	1	reset default value for this field. It is suggested to program this field to 1h.
1	RO	0	(See the Note within the description for the LINK_BW_SET register (DPCD Address 00100h.)
0	RO	0	 Ih = 1 lane (Lane 0 only) 2h = 2 lanes (Lanes 0 and 1 only) 4h = 4 lanes A Source device may choose any lane count as long as it does not exceed the capability of the DPRX. For DPCD Ver.1.0: Bits <7:5> = RESERVED. Read all 0's. For DPCD Ver.1.1: Bits <6:5> = RESERVED. Read all 0's. Bit 7 = ENHANCED_FRAME_EN 0 = Enhanced Framing symbol sequence is not enabled. 1 = Enhanced Framing symbol sequence for BS and SR is enabled. Applicable to SST-only mode. A DPTX must set this bit to 1 when the DPRX has the ENHANCED_FRAME_CAP bit in the MAX_LANE_COUNT register

BYTE 19 - 30 (Reserved)



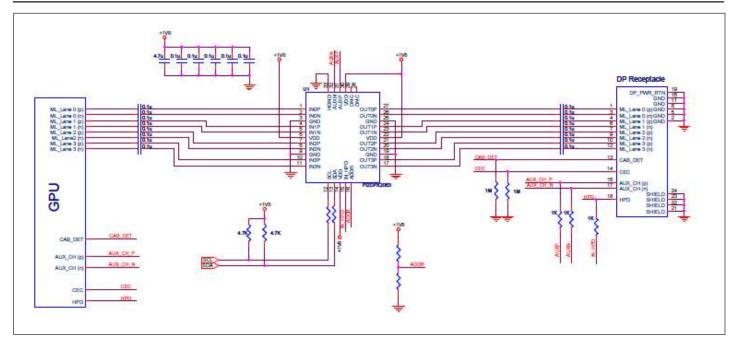


BYTE 31 (D	BYTE 31 (DPCD Address 00600h: SET DP Power)									
Bit	Туре	Power-up Condition	Comment							
7	RO	0	SET_POWER_STATE							
6	RO	0	Bit 2:0							
5	RO	0	-001 = Set local Sink device and all downstream Sink devices to D0 (normal operation mode).							
4	RO	0	010 = Set local Sink device and all downstream Sink devices to D3 (power-							
3	RO	0	down mode). - 101 = Set Main-Link for local Sink device and all downstream Sink devices							
2	RO	0	to D3 (power-down mode), keep AUX block fully powered, ready to reply							
1	RO	0	within a Response Timeout period of 300us.							
0	RO	1	All other values are RESERVED.							





Application Schematics

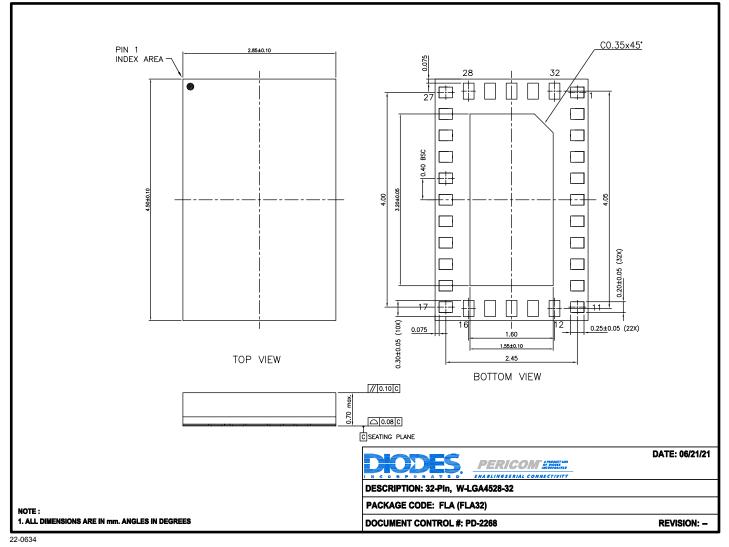






Packaging Mechanical

32-WLGA (FLA)



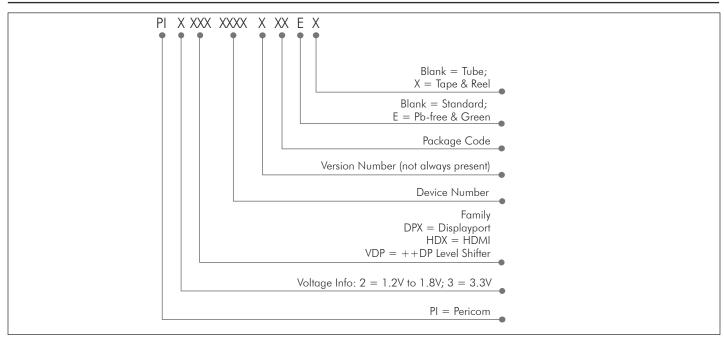
For latest package info.

please check: http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/

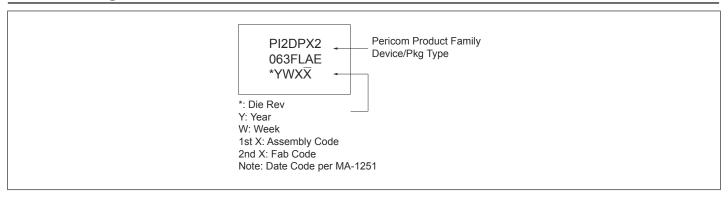




Device Naming Information



Part Marking





A Product Line of Diodes Incorporated



PI2DPX2063

Tape & Reel Materials and Design

Carrier Tape

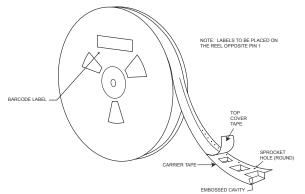
The pocketed carrier tape is made of conductive polystyrene plus carbon material (or equivalent). The surface resistivity is $106\Omega/sq$. maximum. Pocket tapes are designed so that the component remains in position for automatic handling after cover tape is removed. Each pocket has a hole in the center for automated sensing if the pocket is occupied or not, thus facilitating device removal. Sprocket holes along the edge of the center tape enable direct feeding into automated board assembly equipment. See figures 3 and 4 for carrier tape dimensions.

Cover Tape

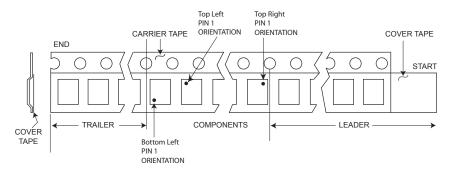
Cover tape is made of anti-static transparent polyester film. The surface resistivity is $107\Omega/sq$. Minimum to $1011\Omega/sq$. maximum. The cover tape is heat-sealed to the edges of the carrier tape to encase the devices in the pockets. The force to peel back the cover tape from the carrier tape shall be a MEAN value of 20gm to 80gm (2N to 0.8N).

Reel

The device loading orientation is in compliance with EIA-481, current version (Figure 2). The loaded carrier tape is wound onto either a 13-inch reel (Figure 4) or 7-inch reel. The reel is made of Antistatic High-Impact Polystyrene. The surface resistivity $107\Omega/sq$. minimum to $1011\Omega/sq$. maximum.



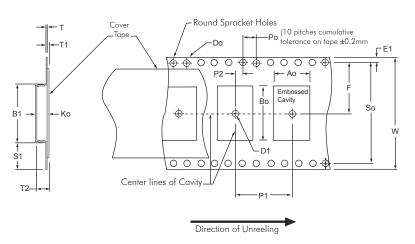
Tape & Reel Label Information



Tape Leader and Trailer Pin 1 Orientations







Standard Embossed Carrier Tape Dimensions

Tape & Reel Dimensions

Constant Dimensions

TAPE SIZE	D ₀	D ₁ (Min)	E1	Po	P ₂	R ⁽²⁾	S ₁ (Min)	T (Max)	T ₁ (Max)
8mm		1.0			2.0 + 0.05	25	0.6	0.6	0.1
12mm					2.0 ± 0.05				
16mm	15.0100	1.5 +0.1-0.0 1.5 1.75 ± 0.1	1.75 ± 0.1	4.0 ± 0.1 2.0 ± 0.1	2.0 ± 0.1	30			
24mm	- 1.5 +0.1-0.0								
32mm						50	N/A ⁽³⁾		
44mm		2.0			2.0 ± 0.15	- 50			

Variable Dimensions

TAPE SIZE	P1	B ₁ (Max)	E ₂ (Min)	F	So	T ₂ (Max)	W (Max)	A ₀ , B ₀ &K ₀
8mm	Specific per package	4.35	6.25	3.5 ± 0.05		2.5	8.3	
12mm	type. Refer to FR-0221 (Tape and Reel Packing Information) or visit	8.2	10.25	5.5 ± 0.05	N/A ⁽⁴⁾	6.5	12.3	
16mm		10.1	14.25	7.5 ± 0.1		8.0	16.3	
24mm	www.diodes.com/assets/	20.1	22.25	11.5 ± 0.1		12.0	24.3	See Note 1
32mm	MediaList-Attachments/ Diodes-Tape-Reel-Tube.	23.0	N/A	14.2 ± 0.1	28.4 ± 0.1	12.0	32.3	
44mm	pdf	35.0	N/A	20.2 ± 0.15	40.4 ± 0.1	16.0	44.3	

NOTES:

A₀, B₀, and K₀ are determined by component size. The cavity must restrict lateral movement of component to 0.5mm maximum for 8mm and 12mm wide tape and 1. to 1.0mm maximum for 16mm, 24mm, 32mm, and 44mm wide carrier. The maximum component rotation within the cavity must be limited to 200 maximum for 8 and 12 mm carrier tapes and 100 maximum for 16mm through 44mm.

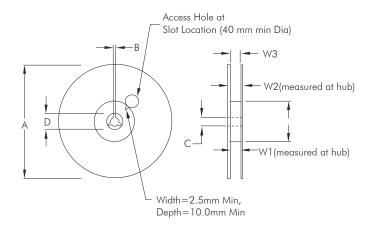
2. Tape and components will pass around reel with radius "R" without damage.

 S_1 does not apply to carrier width \ge 32mm because carrier has sprocket holes on both sides of carrier where $D_0 \ge S_1$. 3.

4. S_0 does not exist for carrier \leq 32mm because carrier does not have sprocket hole on both side of carrier.







Reel Dimensions By Tape Size

TAPE SIZE	Α	N (Min) ⁽¹⁾	W ₁	W ₂ (Max)	W3	B (Min)	С	D (Min)
8mm	178 ± 2.0mm or	60 ± 2.0mm or 100 ± 2.0mm	8.4 +1.5/-0.0mm	14.4mm		1.5mm	13.0 +0.5/-0.2 mm	20.2mm
12mm	330 ± 2.0mm		12.4 +2.0/-0.0mm	18.4mm	Shall Accommodate Tape Width Without Interference			
16mm		nm 100 ± 2.0mm	16.4 +2.0/-0.0mm	22.4mm				
24mm	220 + 2.0		24.4 +2.0/-0.0mm	30.4mm				
32mm	330 ± 2.0mm		32.4 +2.0/-0.0mm	38.4mm				
44mm			44.4 +2.0/-0.0mm	50.4mm				

NOTE:

1. If reel diameter A=178 ±2.0mm, then the corresponding hub diameter (N(min) will by 60 ±2.0mm. If reel diameter A=330±2.0mm, then the corresponding hub diameter (N(min)) will by 100±2.0mm.





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